

Is Now Part of



# **ON Semiconductor**®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor dates sheds, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor dates sheds and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use on similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor and its officers, employees, subsidiaries, affliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any lay bed ON Semiconductor and its officers, employees, ween if such claim alleges that ON Semiconductor was negligent regarding the d

### February 2008

# FAIRCHILD

# FGL40N120AND 1200V NPT IGBT

## Features

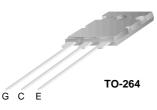
- High speed switching
- Low saturation voltage :  $V_{CE(sat)} = 2.6 \text{ V} @ I_C = 40 \text{ A}$
- High input impedance
- CO-PAK, IGBT with FRD : t<sub>rr</sub> = 75ns (typ.)

## Applications

Induction Heating, UPS, AC & DC motor controls and general purpose inverters.

## Description

Employing NPT technology, Fairchild's AND series of IGBTs provides low conduction and switching losses. The AND series offers an solution for application such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).



### **Absolute Maximum Ratings**

Symbol	Parameter		FGL40N120AND	Units
V <sub>CES</sub>	Collector-Emitter Voltage		1200	V
V <sub>GES</sub>	Gate-Emitter Voltage		±25	V
1	Collector Current	@T <sub>C</sub> = 25°C	64	А
I <sub>C</sub>	Collector Current	@T <sub>C</sub> = 100°C	40	А
I <sub>CM(1)</sub>	Pulsed Collector Current		160	А
I <sub>F</sub>	Diode Continuous Forward Current	@T <sub>C</sub> = 100°C	40	А
I <sub>FM</sub>	Diode Maximum Forward Current		240	А
П	Maximum Power Dissipation	@T <sub>C</sub> = 25°C	500	W
P <sub>D</sub>	Maximum Power Dissipation	@T <sub>C</sub> = 100°C	200	W
SCWT	Short Circuit Withstand Time, $V_{CE} = 600V$ , $V_{GE} = 15V$ , $T_C = 125^{\circ}C$		10	μS
Т <sub>Ј</sub>	Operating Junction Temperature		-55 to +150	°C
T <sub>STG</sub>	Storage Temperature Range		-55 to +150	°C
Τ <sub>L</sub>	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 seconds		300	°C

Notes:

(1) Pulse width limited by max. junction temperature

### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction-to-Case		0.25	°C/W
$R_{\theta JC}(DIODE)$	Thermal Resistance, Junction-to-Case		0.7	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction-to-Ambient		25	°C/W

Device Marking Device Pac		Package	-		e Width	Quantity		
		TO-264					25	
Electrica	al Chai	racteristics of th	ne IGBT T <sub>c</sub>	= 25°C unless otherwise not	ed			
Symbol		Parameter		Conditions		Тур.	Max.	Units
Off Characte	eristics							
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage		age V <sub>GE</sub> = 0\	$V_{GE} = 0V, I_C = 1mA$				V
BV <sub>CES</sub> / ΔT <sub>J</sub>	Tempera Voltage	ture Coefficient of Break	down	$V_{GE} = 0V, I_C = 1mA$		0.6		V/°C
I <sub>CES</sub>	Collector	r Cut-Off Current	$V_{CE} = V_{CE}$	$V_{CE} = V_{CES}, V_{GE} = 0V$ $V_{GE} = V_{GES}, V_{CE} = 0V$			1 ±250	mA nA
I <sub>GES</sub>	G-E Lea	kage Current						
On Characte	eristics							·
V <sub>GE(th)</sub>	n Characteristics GE(th) G-E Threshold Voltage		I <sub>C</sub> = 250	I <sub>C</sub> = 250μA, V <sub>CE</sub> = V <sub>GE</sub>		5.5	7.5	V
02()			-	$I_{\rm C} = 40$ A, $V_{\rm GE} = 15$ V		2.6	3.2	V
V <sub>CE(sat)</sub> Collector to Emitter Saturation Voltage		I <sub>C</sub> = 40A	$I_{C} = 40A, V_{GE} = 15V,$ $T_{C} = 125^{\circ}C$		2.9		V	
		$I_{\rm C} = 64 {\rm A}$	, V <sub>GE</sub> = 15V		3.15		V	
Dynamic Ch	naracteris	tics						
C <sub>ies</sub>	Input Capacitance		۱ <i>۲</i> ۵۵			3200		pF
C <sub>oes</sub>	Output C	Capacitance		V <sub>CE</sub> = 30V, V <sub>GE</sub> = 0V f = 1MHz		370		pF
C <sub>res</sub>	Reverse Transfer Capacitance					125		pF
Switching C	haracteri	istics						
t <sub>d(on)</sub>	r	Delay Time		V <sub>CC</sub> = 600V, I <sub>C</sub> = 40A,		15		ns
t <sub>r</sub>	Rise Tim	e				20		ns
t <sub>d(off)</sub>	Turn-Off	Delay Time	$V_{cc} = 60$			110		ns
t <sub>f</sub>	Fall Time	9	$R_{G} = 5\Omega$	, V <sub>GE</sub> = 15V,		40	80	ns
Eon	Turn-On	Switching Loss	Inductive	e Load, T <sub>C</sub> = 25°C		2.3	3.45	mJ
E <sub>off</sub>	Turn-Off	Switching Loss				1.1	1.65	mJ
E <sub>ts</sub>	Total Sw	itching Loss				3.4	5.1	mJ
t <sub>d(on)</sub>	Turn-On	Delay Time				20		ns
t <sub>r</sub>	Rise Tim	e				25		ns
t <sub>d(off)</sub>	Turn-Off	Delay Time	V <sub>CC</sub> = 60	V <sub>CC</sub> = 600V, I <sub>C</sub> = 40A,		120		ns
t <sub>f</sub>	Fall Time	9	$R_{G} = 5\Omega$	, V <sub>GE</sub> = 15V,		45		ns
E <sub>on</sub>	Turn-On	Switching Loss	Inductive	Inductive Load, T <sub>C</sub> = 125°C		2.5		mJ
E <sub>off</sub>	Turn-Off	Switching Loss				1.8		mJ
E <sub>ts</sub>	Total Sw	itching Loss				4.3		mJ
Qg	Total Ga	te charge	\/			220	330	nC
Q <sub>ge</sub>	Gate-Em	nitter Charge	V <sub>CE</sub> = 60 V <sub>GE</sub> = 15	00V, I <sub>C</sub> = 40A, 5V		25	38	nC
Q <sub>gc</sub>	Gate-Co	llector Charge	- GE - R			130	195	nC

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Units
V <sub>FM</sub>	Diode Forward Voltage	I <sub>F</sub> = 40A	$T_C = 25^{\circ}C$		3.2	4.0	- V
			T <sub>C</sub> = 125°C		2.7		
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>F</sub> = 40A, di/dt = 200A/μs	$T_{\rm C} = 25^{\circ}{\rm C}$		75	112	nS
			T <sub>C</sub> = 125°C		130		
Irr	Diode Peak Reverse Recovery Current		$T_{C} = 25^{\circ}C$		8	12	Α
			T <sub>C</sub> = 125°C		13		
Q <sub>rr</sub>	Diode Reverse Recovery Charge		$T_C = 25^{\circ}C$		300	450	nC
			T <sub>C</sub> = 125°C		845		

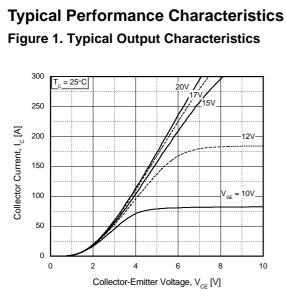


Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level

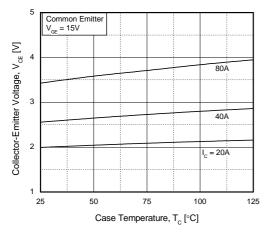


Figure 5. Saturation Voltage vs.  $V_{GE}$ 

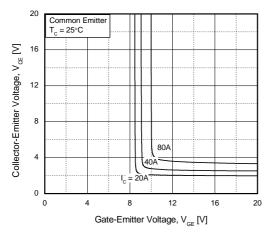


Figure 2. Typical Saturation Voltage Characteristics

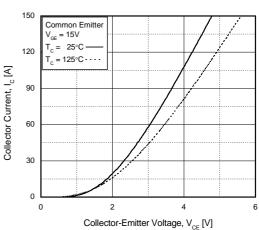


Figure 4. Load Current vs. Frequency

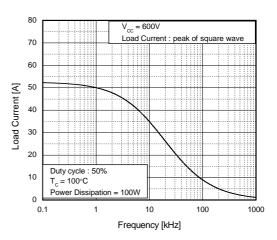
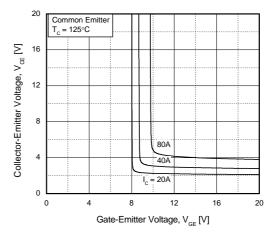
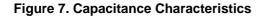


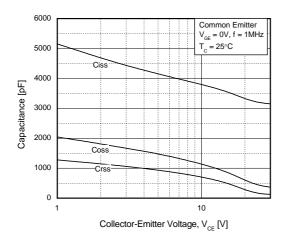
Figure 6. Saturation Voltage vs. V<sub>GE</sub>



FGL40N120AND 1200V NPT IGBT

## Typical Performance Characteristics (Continued)







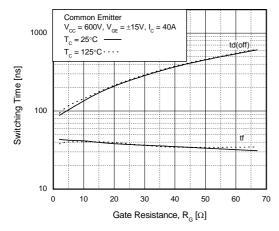


Figure 11. Turn-On Characteristics vs. Collector Current

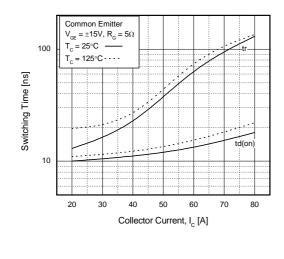


Figure 8. Turn-On Characteristics vs. Gate Resistance

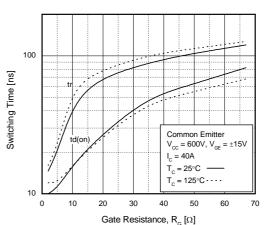


Figure 10. Switching Loss vs. Gate Resistance

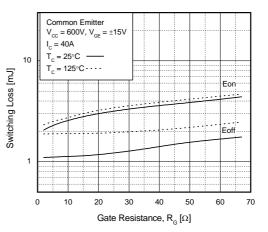
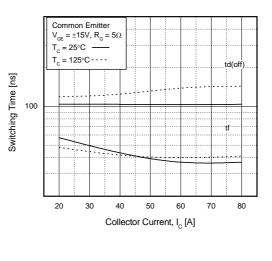


Figure 12. Turn-Off Characteristics vs. Collector Current



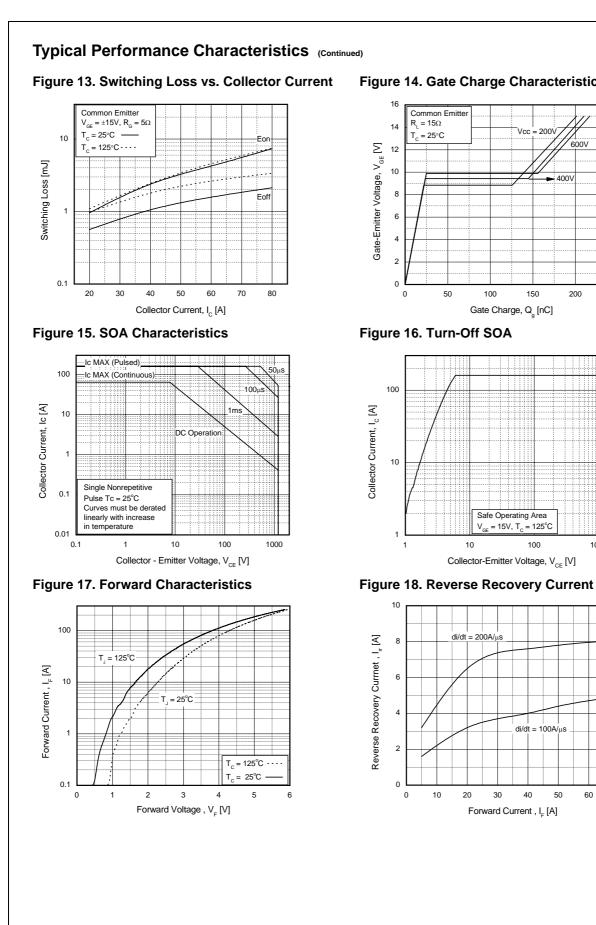
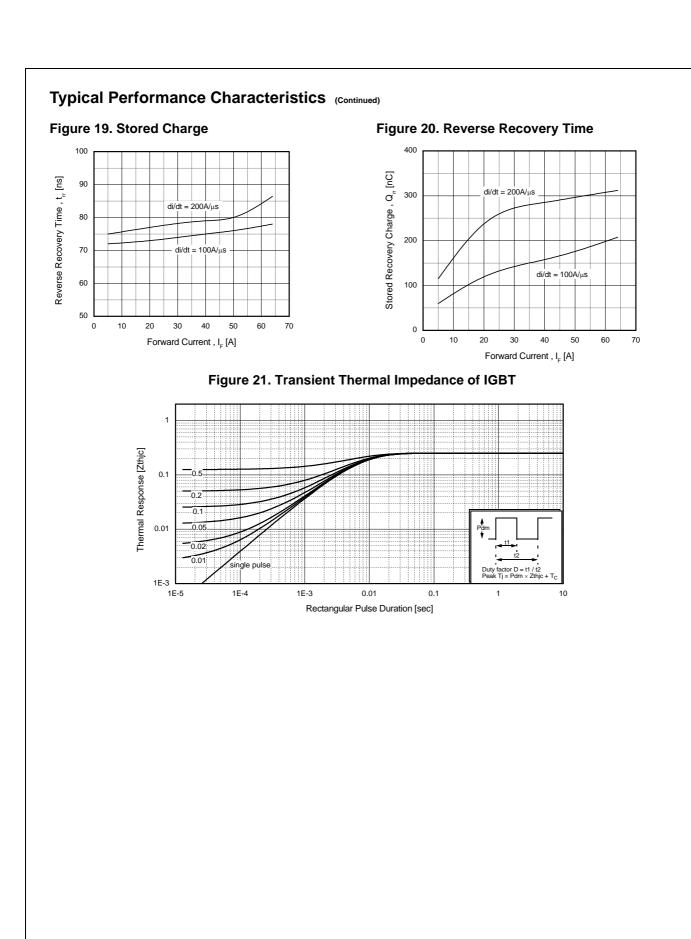


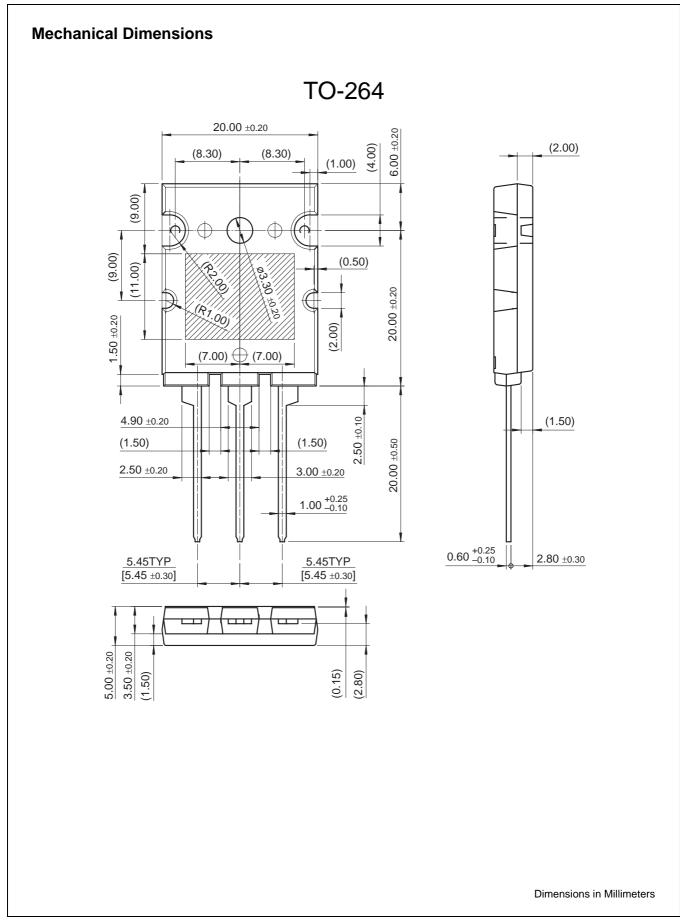
Figure 14. Gate Charge Characteristics

600V

400\

FGL40N120AND 1200V NPT IGBT





8

FGL40N120AND Rev. A2



### SEMICONDUCTOR®

### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidianries, and is not intended to be an exhaustive list of all such trademarks.

PDP-SPM™

ACEx®
Build it Now™
CorePLUS™
CROSSVOLT™
CTL™
Current Transfer Logic™
EcoSPARK <sup>®</sup>
EZS\\/ITCH™ *

EZSWITCH<sup>™</sup>

Fairchild<sup>®</sup> Fairchild Semiconductor<sup>®</sup> FACT Quiet Series<sup>™</sup> FACT<sup>®</sup> FAST<sup>®</sup> FastvCore<sup>™</sup> FlashWriter<sup>®</sup> \* **FRFET**® Global Power Resource<sup>SM</sup> Green FPS™ Green FPS<sup>™</sup> e-Series<sup>™</sup> GTO™ i-Lo™ IntelliMAX™ **ISOPLANAR™** MegaBuck™ MICROCOUPLER™ MicroFET™ MicroPak™ MillerDrive™ Motion-SPM™ **OPTOLOGIC**<sup>®</sup> **OPTOPLANAR**<sup>®</sup> R

FPS™

Power220<sup>®</sup> POWEREDGE<sup>®</sup> Power-SPM<sup>™</sup> PowerTrench® Programmable Active Droop<sup>™</sup> **QFET<sup>®</sup>** QS™ QT Optoelectronics™ Quiet Series™ RapidConfigure™ SMART START™ SPM® STEALTH™ SuperFET™ SuperSOT™-3 SuperSOT™-6 SuperSOT™-8

SupreMOS™ SyncFET™ The Power Franchise<sup>®</sup> pwer franchise TinyBoost™ TinyBuck™ TinyLogic® TINYOPTO™ TinyPower™ TinyPWM™ TinyWire™ µSerDes™ UHC® Ultra FRFET™ UniFET™ VCX™

\* EZSWITCH<sup>TM</sup> and FlashWriter<sup>®</sup> are trademarks of System General Corporation, used under license by Fairchild Semiconductor.

### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- 2. A critical component in any component of a life support, device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

Datasheet Identification	Product Status	Definition			
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.			
Preliminary First Production		This datasheet contains preliminary data; supplementary data will be pub- lished at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.			
		This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.			
Obsolete Not In Production		This datasheet contains specifications on a product that has been discontin- ued by Fairchild Semiconductor. The datasheet is printed for reference infor- mation only.			

## PRODUCT STATUS DEFINITIONS

### www.fairchildsemi.com